2022년 1월 26일(수), 10:45-12:30 Room F (스페이드 I, 6층)

G. Device & Process Modeling, Simulation and Reliability 분과 [WF2-G] Ab-initio Simulation and Quantum Transport

좌장: 홍성민 교수(GIST), 장지원 교수(연세대학교)

WF2-G-1 10:45-11:15	Spin Circuit Model and Its Applications Seokmin Hong Center for Spintronics, KIST
WF2-G-2 11:15-11:30	Quantum Transport Simulation of Nanosheet FETs with Various Cross-sections Including Electron-phonon Scattering Phil-Hun Ahn and Sung-Min Hong School of Electrical Engineering and Computer Science, GIST
WF2-G-3 11:30-11:45	Short Channel Effects Induced by the Multi-domain in Negative Capacitance Field-Effect Transistors: A Phase-field Based Quantum Transport Study Hyeongu Lee and Mincheol Shin Department of Electrical Engineering, KAIST
WF2-G-4 11:45-12:00	Design of Noise-Robust Entangling Quantum Logic Gates Using Electrode- Driven Silicon Quantum Dot Platform Hoon Ryu and Ji-Hoon Kang KISTI
WF2-G-5 12:00-12:15	Computational Analysis of Bi ₂ O ₂ Se-Metal Contact Sukhyeong Youn and Jiwon Chang ¹ Department of System Semiconductor Engineering, Yonsei University, ² Department of Materials Science & Engineering, Yonsei University
WF2-G-6 12:15-12:30	Landau Coefficients Extraction of Slab BaTiO₃ in Ferroelectric-Insulator Nanocapacitors Jeonghwan Jang, Junbeom Seo, and Mincheol Shin School of Electrical Engineering, KAIST